

Pranab Biswas

List of Publications by Year in descending order

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28
papers

436
citations

840776

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all docs

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docs citations

28
times ranked

728
citing authors

#	ARTICLE	IF	CITATIONS
1	Low-Temperature Facile Synthesis of Sb-Doped p-Type ZnO Nanodisks and Its Application in Homo Junction Light-Emitting Diode. ACS Applied Materials & Interfaces, 2016, 8, 13018-13026.	8.0	58
2	Super rapid response of humidity sensor based on MOCVD grown ZnO nanotips array. Sensors and Actuators B: Chemical, 2013, 178, 331-338.	7.8	55
3	Solution-processed n-ZnO nanorod/p-Co ₃ O ₄ nanoplate heterojunction light-emitting diode. Applied Surface Science, 2017, 406, 192-198.	6.1	46
4	Lead-free epitaxial ferroelectric material integration on semiconducting (100) Nb-doped SrTiO ₃ for low-power non-volatile memory and efficient ultraviolet ray detection. Scientific Reports, 2015, 5, 12415.	3.3	42
5	Au/p-Si Schottky junction solar cell: Effect of barrier height modification by InP quantum dots. Solar Energy Materials and Solar Cells, 2015, 132, 230-236.	6.2	39
6	Tuning of oxygen vacancy-induced electrical conductivity in Ti-doped hematite films and its impact on photoelectrochemical water splitting. Scientific Reports, 2020, 10, 7463.	3.3	28
7	Improved UV response of ZnO nanotubes by resonant coupling of anchored plasmonic silver nanoparticles. Nanotechnology, 2017, 28, 225502.	2.6	18
8	Oxygen vacancy-induced red light emission from flexible inorganic micropatterned p-CuO/n-ZnO heterojunction light-emitting diode. Applied Physics Letters, 2016, 109, .	3.3	14
9	Low temperature solution process-based defect-induced orange-red light emitting diode. Scientific Reports, 2015, 5, 17961.	3.3	13
10	An alternative approach to investigate the origin of p-type conductivity in arsenic doped ZnO. Current Applied Physics, 2015, 15, 1256-1261.	2.4	13
11	A study on electrical transport vis-à-vis the effect of thermal annealing on the p-type conductivity in arsenic-doped MOCVD grown ZnO in the temperature range 10 ^o –300K. Journal of Alloys and Compounds, 2013, 552, 304-309.	5.5	11
12	Effect of band offset on carrier transport and infrared detection in InP quantum dots/Si nano-heterojunction grown by metalorganic chemical vapor deposition technique. Journal of Applied Physics, 2014, 115, .	2.5	11
13	Adopting Novel Strategies in Achieving High-Performance Single-Layer Network Structured ZnO Nanorods Thin Film Transistors. ACS Applied Materials & Interfaces, 2016, 8, 11564-11574.	8.0	11
14	Charge storage properties of InP quantum dots in GaAs metal-oxide-semiconductor based nonvolatile flash memory devices. Applied Physics Letters, 2012, 101, 212108.	3.3	10
15	GaAs metal-oxide-semiconductor based nonvolatile memory devices embedded with ZnO quantum dots. Journal of Applied Physics, 2013, 114, 084509.	2.5	10
16	Direct Transfer Printing with Metal Oxide Layers for Fabricating Flexible Nanowire Devices. Advanced Functional Materials, 2015, 25, 6921-6926.	14.9	10
17	Efficient Resistive Switching and Spike Rate Dependent Plasticity in a New CuCrO ₂ Memristor for Plausible Neuromorphic Systems. IEEE Transactions on Electron Devices, 2020, 67, 3451-3458.	3.0	10
18	Device characteristics of amorphous indium-gallium-zinc-oxide channel capped with silicon oxide passivation layers. Materials Science in Semiconductor Processing, 2016, 49, 34-39.	4.0	9

#	ARTICLE	IF	CITATIONS
19	Enhanced photoluminescence in electrodeposited NiO nanowalls mediated by plasmonic Au nanoparticle. <i>Materials Chemistry and Physics</i> , 2017, 201, 63-68.	4.0	8
20	Understanding the efficacy of Cu in creating oxygen vacancies and temperature dependent electrical transport in solution processed Cu:ZnO thin films. <i>Materials Science in Semiconductor Processing</i> , 2020, 120, 105311.	4.0	8
21	InAs quantum dots as charge storing elements for applications in flash memory devices. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2015, 198, 102-107.	3.5	5
22	Anomalous diffusion of Ga and As from semi-insulating GaAs substrate into MOCVD grown ZnO films as a function of annealing temperature and its effect on charge compensation. <i>AIP Advances</i> , 2014, 4, 057108.	1.3	4
23	Effect of band alignment on photoluminescence and carrier escape from InP surface quantum dots grown by metalorganic chemical vapor deposition on Si. <i>Journal of Applied Physics</i> , 2014, 115, 043101.	2.5	2
24	Varying Photoconductivity of ZnO as a Function of Annealing Temperature. <i>Environmental Science and Engineering</i> , 2014, , 819-821.	0.2	1
25	Photoluminescence study based prediction on visible luminescence from n-Zno/p-GaAs heterojunction. , 2014, , .		0
26	Fabrication and characterization of p-Si/n-ZnO heterojunction ultraviolet photodetector. <i>AIP Conference Proceedings</i> , 2015, , .	0.4	0
27	Photovoltaic conversion of visible spectrum by GaP capped InP quantum dots grown on Si (100) by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2015, 106, 012103.	3.3	0
28	Fabrication of n-ZnO/p-GaAs Heterojunction and Prediction of Its Luminescence Based on Photoluminescence Study. <i>Environmental Science and Engineering</i> , 2014, , 815-818.	0.2	0